

IN THE CLAIMS

What is claimed is

- 1 **1.** A method of verifying a reticle, comprising the steps of:
2 forming a conformal layer over a non-resist deposited layer that is formed on
3 a uniform surface, the deposited layer including a reticle pattern; and
4 inspecting the reticle pattern for defects.
- 1 **2.** The method of claim 1, wherein:
2 the conformal layer comprises a conductive material.
- 1 **3.** The method of claim 2, wherein:
2 the conformal layer comprises titanium.
- 1 **4.** The method of claim 3, wherein:
2 the conformal layer comprises a layer of titanium nitride formed over a layer
3 of titanium.
- 1 **5.** The method of claim 2, wherein:
2 the reticle pattern in the deposited layer includes features having a minimum
3 size L, and the conformal layer has a thickness of no more than $1/2L$.

- 1 **6.** The method of claim 2, wherein:
2 the conformal layer has a thickness of no more than 1000Å.
- 1 **7.** The method of claim 1, wherein:
2 the deposited layer comprises silicon oxide.
- 1 **8.** The method of claim 7, wherein:
2 the deposited layer comprises a layer of undoped silicon dioxide formed on a
3 layer of phosphosilicate glass.
- 1 **9.** The method of claim 1, wherein:
2 the thickness of the deposited layer is greater than 2500Å.
- 1 **10.** The method of claim 1, wherein:
2 the thickness of the deposited layer is greater than 5000Å.
- 1 **11.** The method of claim 1, wherein:
2 the uniform surface comprises a silicon substrate.

1 **12.** A method of verifying a reticle, comprising the steps of:

2 forming a conductive conformal layer greater than 100Å over a deposited

3 layer patterned with a reticle; and

4 inspecting the pattern in the deposited layer.

1 **13.** The method of claim 12, wherein:

2 inspecting the pattern comprises automatically inspecting the pattern with

3 pattern inspection equipment.

1 **14.** The method of claim 12, wherein:
2 automatically inspecting the pattern includes automatically aligning a wafer in
3 the pattern inspection equipment with the pattern formed in the deposited layer.

1 **15.** The method of claim 12, wherein:
2 the pattern comprises a contact reticle pattern.

1 **16.** The method of claim 12, further including:

2 patterning the deposited layer with the reticle includes

3 patterning a layer of resist formed over the deposited layer with the

4 reticle pattern,

5 etching the deposited layer, and

6 removing the resist.

